# MICROWAVE POWER GaAs FET TIM1011-8ULA

#### **FEATURES**

- ·BROAD BAND INTERNALLY MATCHED FET ·HIGH POWER
- P1dB= 39.5dBm at 10.7GHz to 11.7GHz

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·HIGH GAIN

G1dB= 9.0dB at 10.7GHz to 11.7GHz

**·LOW INTERMODULATION DISTORTION** 

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IM3(MIN.) = -42dBc at Pout= 27.0dBm (Single Carrier Level)
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·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.	
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 2.0A f= 10.7 to 11.7GHz Two-Tone Test Po= 27dBm, ∆f= 5MHz (Single Carrier Level)	dBm	38.5	39.5	_	
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	9.0		
Drain Current	IDS1		А		2.0	2.5	
Gain Flatness	ΔG		dB			±0.8	
Power Added Efficiency	ηadd		%		39		
3rd Order Intermodulation Distortion	IM3		dBc	-42	-45		
Drain Current	IDS2		А		2.0	2.5	
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C			80	

#### RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance(Rg): 100  $\Omega$ 

### ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 2.4A	S	_	2.0	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 72mA	V	-0.5	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А		4.0	
Gate-Source Breakdown Voltage	VGSO	IGS= -72μA	V	-5	_	_
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	_	3.0	3.7

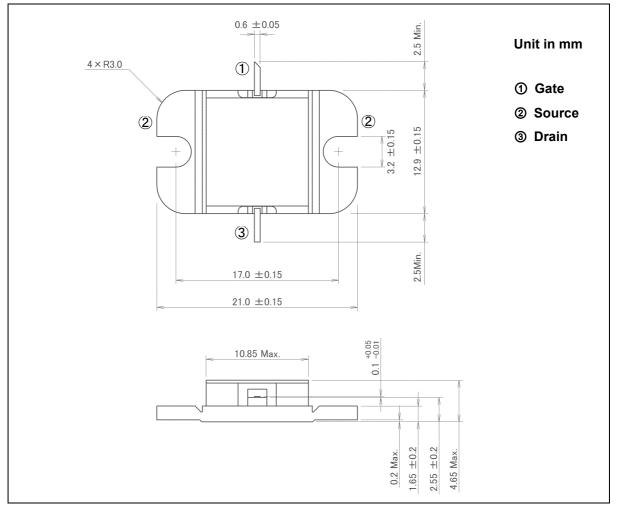
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## ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	5.7
Total Power Dissipation (Tc= 25°C)	PT	W	40.5
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

### PACKAGE OUTLINE (2-11C1B)



#### HANDLING PRECAUTIONS FOR PACKAGE MODEL

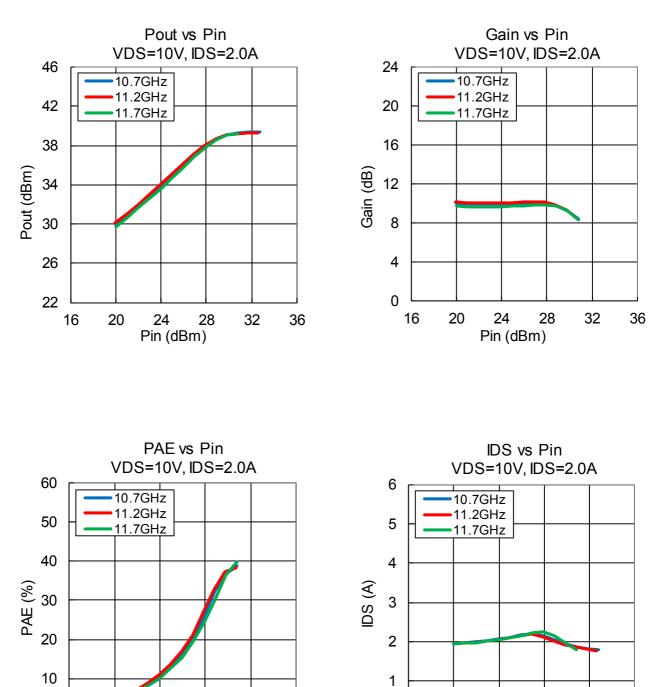
Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

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MICROWAVE SEMICONDUCTOR TECHNICAL DATA

#### ·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 2.0 A, f= 10.7, 11.2, 11.7 GHz, Ta= +25 °C



0

16

20

24

Pin (dBm)

28

32

36

24

Pin (dBm)

20

0

16

28

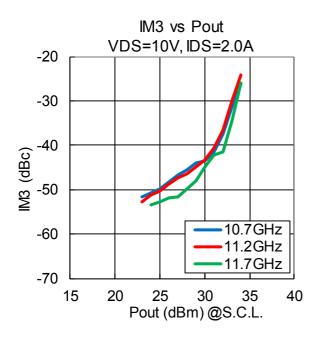
32

36

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·IM3 vs. Pout

VDS= 10 V, IDSset= 2.0 A, f= 10.7, 11.2, 11.7 GHz, Δf= 5 MHz , Ta= +25 °C

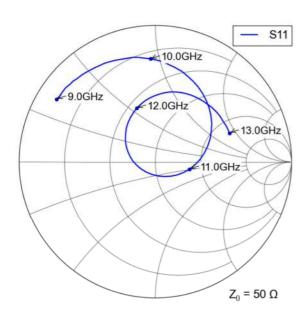


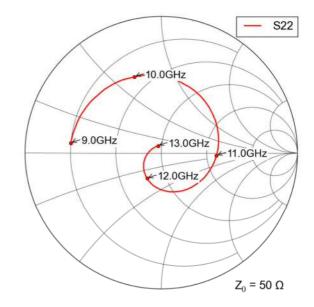
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

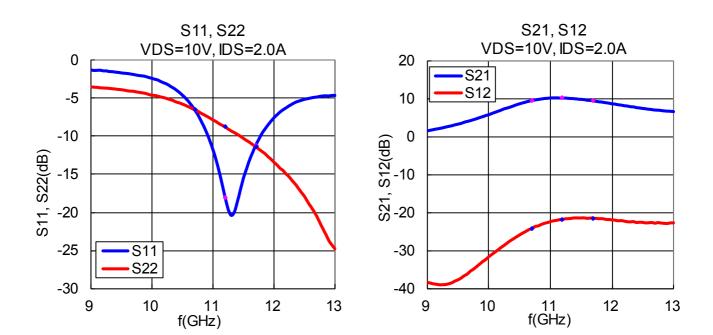
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#### ·S-Parameters

VDS= 10 V, IDSset= 2.0 A, f= 9.0 to 13.0 GHz, Ta= +25 °C







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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